



## N-Channel 60 V (D-S) Super Junction MOSFET

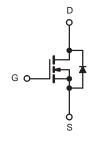
| PRODUCT SUMMARY     |                                  |                                 |                       |  |  |  |
|---------------------|----------------------------------|---------------------------------|-----------------------|--|--|--|
| V <sub>DS</sub> (V) | $R_{DS(on)}$ (m $\Omega$ )(Typ.) | I <sub>D</sub> (A) <sup>a</sup> | Q <sub>g</sub> (Typ.) |  |  |  |
| 60                  | 1.1 at V <sub>GS</sub> = 10 V    | 0 V 335 209 n                   |                       |  |  |  |
|                     | 1.5 at V <sub>GS</sub> = 4.5 V   | 333                             | 209 nC                |  |  |  |

#### **FEATURES**

- DT- SJ Power MOSFET
- 100 %  $R_q$  and UIS Tested
- Lead-Free, RoHS Compliant
- Low RDS(ON)

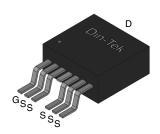
#### **APPLICATIONS**

- · Battery powered circuits
- BLDC Motor drive applications



N-Channel MOSFET

| TO-263-6L Pin Configuration |
|-----------------------------|
| Top View                    |



| ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted) |                                   |                  |      |   |  |  |  |
|---|-----------------------------------|------------------|------|---|--|--|--|
| PARAMETER   | SYMBOL                            | LIMIT            | UNIT |   |  |  |  |
| Drain-Source Voltage  | V <sub>DS</sub>                   | 60               | V    |   |  |  |  |
| Gate-Source Voltage   | V <sub>GS</sub>                   | ± 20             |      |   |  |  |  |
| Continuous Dunin Courset /T 475 90\2                                      | T <sub>C</sub> = 25 °C            |                  | 335  | А |  |  |  |
| Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>a</sup>           | T <sub>C</sub> = 100 °C           | - I <sub>D</sub> | 265  |   |  |  |  |
| Pulsed Drain Current <sup>b</sup>   | I <sub>DM</sub>                   | 1340             |      |   |  |  |  |
| Single Avalanche Energy   | E <sub>AS</sub>                   | 1010             | mJ   |   |  |  |  |
| Maximum Power Dissipation <sup>c</sup>                                    | T <sub>C</sub> = 25 °C            | В                | 365  | W |  |  |  |
| waximum rower bissipation   | T <sub>C</sub> = 100 °C           | - P <sub>D</sub> | 183  |   |  |  |  |
| Operating Junction and Storage Temperature                                | T <sub>J</sub> , T <sub>stg</sub> | - 55 to + 175    | °C   |   |  |  |  |

| THERMAL RESISTANCE RATINGS                   |                   |       |      |  |  |  |
|--|-------------------|-------|------|--|--|--|
| PARAMETER                                    |                   | LIMIT | UNIT |  |  |  |
| Junction-to-Ambient (PCB Mount) <sup>d</sup> | R <sub>thJA</sub> | 40    | °C/W |  |  |  |
| Junction-to-Case (Drain)                     | R <sub>thJC</sub> | 0.41  |      |  |  |  |

#### **Notes**

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c.  $\,$  Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R<sub>8JA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



| <b>SPECIFICATIONS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted) |                     |  |      |       |       |      |  |
|--|---------------------|--|------|-------|-------|------|--|
| PARAMETER  | SYMBOL              | TEST CONDITIONS  | MIN. | TYP.  | MAX.  | UNIT |  |
| Static   |                     |  |      |       |       |      |  |
| Drain-Source Breakdown Voltage   | V <sub>DS</sub>     | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$                      | 60   | -     | -     | V    |  |
| Gate Threshold Voltage   | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}, I_D = 250 \mu A$                                 | 1    | -     | 3     | V    |  |
| Gate-Body Leakage  | I <sub>GSS</sub>    | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$                  | -    | -     | ± 100 | nA   |  |
| Zero Gate Voltage Drain Current  |                     | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V                      | -    | -     | 1     | μΑ   |  |
| Zero Gate Voltage Drain Guirent  | I <sub>DSS</sub>    | Vps = 48 V, Vgs = 0 V, Tj = 55 °C                                  | -    | -     | 100   |      |  |
| On-State Drain Current <sup>a</sup>                                    | I <sub>D(on)</sub>  | $V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$                    | 335  | -     | -     | Α    |  |
| Drain-Source On-State Resistance <sup>a</sup>                          | R <sub>DS(on)</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 50 A - 1.1                |      | 1.1   | 1.4   | m0   |  |
| Drain Godice on Glate Resistance                                       | NDS(on)             | $V_{GS} = 4.5 \text{ V}, I_D = 50 \text{ A}$                       | -    | 1.5   | 1.9   | mΩ   |  |
| Forward Transconductance <sup>a</sup>                                  | 9 <sub>fs</sub>     | V <sub>DS</sub> = 5 V, I <sub>D</sub> = 50 A                       | -    | 192   | -     | S    |  |
| Dynamic <sup>b</sup>   |                     |  |      |       |       |      |  |
| Input Capacitance  | C <sub>iss</sub>    |  | -    | 11900 | -     | pF   |  |
| Output Capacitance   | C <sub>oss</sub>    | $V_{GS} = 0 \text{ V}, V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$   | -    | 2640  | -     |      |  |
| Reverse Transfer Capacitance   | C <sub>rss</sub>    |  | -    | 238   | -     |      |  |
| Total Gate Charge <sup>c</sup>   | $Q_g$               |  | -    | 209   | -     | nC   |  |
| Gate-Source Charge <sup>c</sup>  | Q <sub>gs</sub>     | $V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$ | -    | 25    | -     |      |  |
| Gate-Drain Charge <sup>c</sup>   | $Q_{gd}$            |  | -    | 43    | -     |      |  |
| Gate Resistance  | $R_g$               | f = 1 MHz  | -    | 0.88  | -     | Ω    |  |
| Turn-On Delay Time <sup>c</sup>  | t <sub>d(on)</sub>  |  | -    | 25    | -     |      |  |
| Rise Time <sup>c</sup>   | t <sub>r</sub>      | $V_{DD} = 30 \text{ V}, I_D = 50 \text{ A}, R_g = 3 \Omega$        | -    | 98    | -     | ns   |  |
| Turn-Off Delay Time <sup>c</sup>                                       | t <sub>d(off)</sub> | V <sub>GS</sub> = 10 V   | -    | 160   | -     |      |  |
| Fall Time <sup>c</sup>   | t <sub>f</sub>      |  | -    | 75    | -     |      |  |
| Drain-Source Body Diode Ratings and                                    | Characterist        | ics <sup>b</sup> (T <sub>C</sub> = 25 °C)                          |      |       |       |      |  |
| Continuous Source-Drain Diode Current                                  | I <sub>S</sub>      | T <sub>C</sub> = 25 °C   | -    | -     | 335   | Α    |  |
| Pulsed Current   | I <sub>SM</sub>     |  | -    | -     | 1340  | Α    |  |
| Forward Voltage <sup>a</sup>   | V <sub>SD</sub>     | I <sub>F</sub> = 1 A, V <sub>GS</sub> = 0 V                        | -    | -     | 1.2   | ٧    |  |
| Reverse Recovery Time  | t <sub>rr</sub>     | I <sub>F</sub> = 50 A, di/dt = 100 A/μs                            | -    | 45    | -     | ns   |  |
| Reverse Recovery Charge  | Q <sub>rr</sub>     |  |      | 63    | -     | nC   |  |

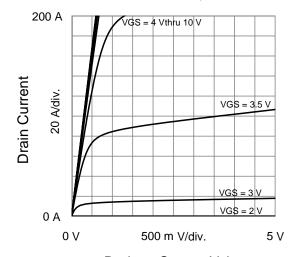
#### Notes

- a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

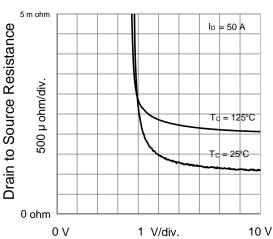
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended pe riods may affect device reliability.



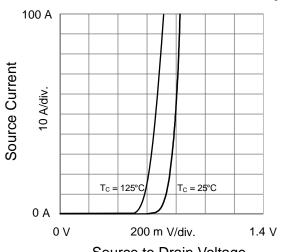
#### TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)



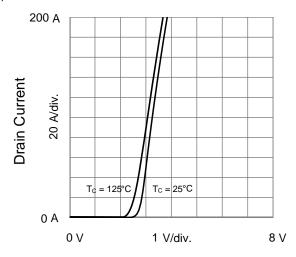
Drain to Source Voltage Output Characteristics



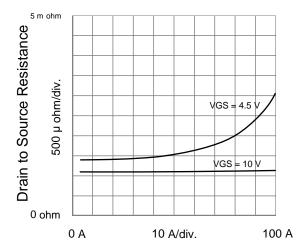
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



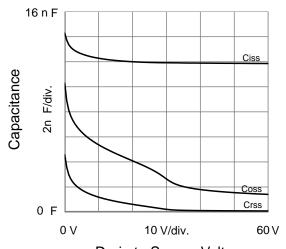
Source to Drain Voltage
Body Diode Forward Characteristics



Gate to Source Voltage Transfer Characteristics



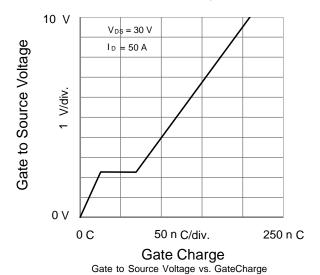
**Drain Current** 

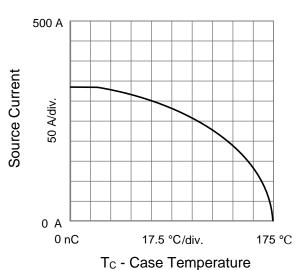


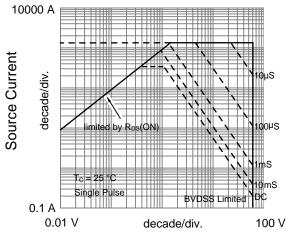
Drain to Source Voltage Capacitances



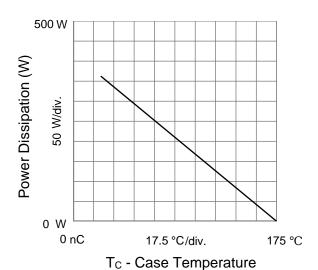
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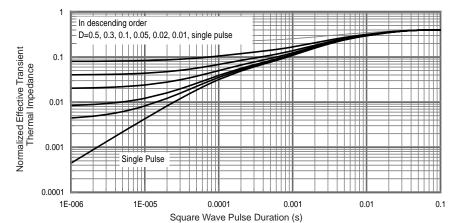






Source to Drain Voltage Safe Operating Area, Junction-to-Case

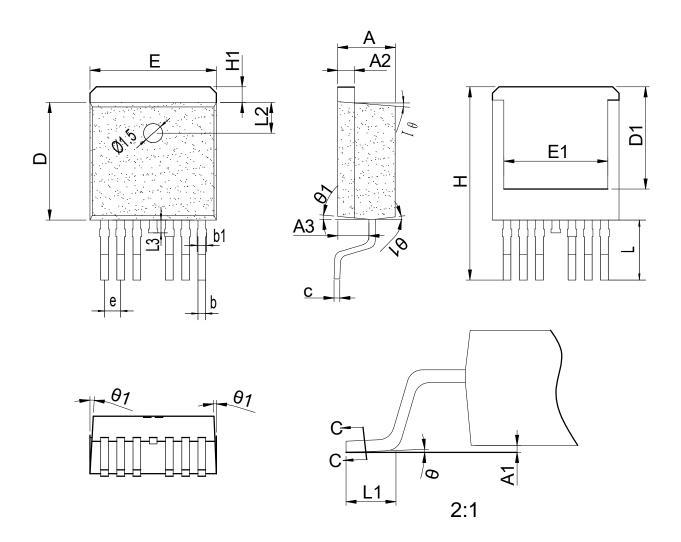




Normalized Thermal Transient Impedance, Junction-to-Case



# TO-263-6L PACKAGE OUTLINE



### Unit:mm

| SYMBOL | MIN  | TYP   | MAX   | SYMBOL | MIN   | TYP   | MAX   |
|--------|------|-------|-------|--------|-------|-------|-------|
| Α      | 4.30 | 4.40  | 4.50  | E1     | 8.40  | 8.60  | 8.80  |
| A1     | 0.00 | 0.10  | 0.20  | е      | 1.25  | 1.27  | 1.29  |
| A2     | 1.22 | 1.27  | 1.32  | Н      | 14.85 | 15.00 | 15.15 |
| A3     | 2.30 | 2.40  | 2.50  | H1     | 0.90  | 1.00  | 1.10  |
| b      | 0.50 | 0.60  | 0.70  | L      | 4.50  | 4.70  | 4.90  |
| b1     | 0.60 | 0.75  | 0.90  | L1     | 2.40  | 2.70  | 3.00  |
| С      | 0.45 | 0.50  | 0.55  | L2     | 2.20  | 2.30  | 2.40  |
| D      | 9.10 | 9.20  | 9.30  | L3     | 0.85  | 1.00  | 1.15  |
| D1     | 7.80 | 8.00  | 8.20  | θ      | 0°    | 2.5°  | 8°    |
| Е      | 9.80 | 10.00 | 10.20 | θ1     | 5°    | 7°    | 9°    |





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